

# FDMB506P

## P-Channel 1.8V Logic Level PowerTrench® MOSFET

### General Description

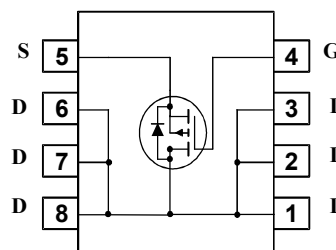
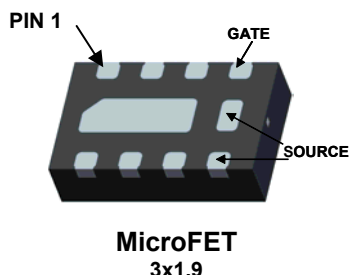
This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance. These devices are well suited for portable electronics applications.

### Applications

- Load switch
- DC/DC Conversion

### Features

- -6.8 A, -20V.  $R_{DS(ON)} = 30\text{ m}\Omega @ V_{GS} = -4.5\text{V}$   
 $R_{DS(ON)} = 38\text{ m}\Omega @ V_{GS} = -2.5\text{V}$   
 $R_{DS(ON)} = 70\text{ m}\Omega @ V_{GS} = -1.8\text{V}$
- Low profile – 0.8 mm maximum
- Fast switching
- RoHS compliant



### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage	-20	V
V <sub>GSS</sub>	Gate-Source Voltage	±8	V
I <sub>D</sub>	Drain Current – Continuous (Note 1a)	-6.8	A
	– Pulsed	70	
P <sub>D</sub>	Power Dissipation (Note 1a)	1.9	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	65	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1b)	208	

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
506	FDMB506P	7"	8mm	3000 units

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-13		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
$I_{GSS}$	Gate–Body Leakage	$V_{GS} = \pm 8\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.4	-0.7	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5\text{ V}, I_D = -6.8\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -2.5\text{ A}$ $V_{GS} = -1.8\text{ V}, I_D = -1.8\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -6.8\text{ A}, T_J = 125^\circ\text{C}$		25 30 40 36	30 38 70 44	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -6.8\text{ A}$		26		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$		2216	2960	pF
$C_{oss}$	Output Capacitance	$f = 1.0\text{ MHz}$		351	470	pF
$C_{rss}$	Reverse Transfer Capacitance			167	260	pF

### Switching Characteristics (Note 2)

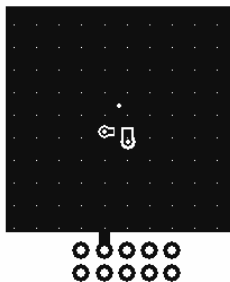
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -10\text{ V}, I_D = -1\text{ A},$		14	25	ns
$t_r$	Turn–On Rise Time	$V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$		8	16	ns
$t_{d(off)}$	Turn–Off Delay Time			175	280	ns
$t_f$	Turn–Off Fall Time			80	128	ns
$Q_g$	Total Gate Charge	$V_{DS} = -10\text{ V}, I_D = -6.8\text{ A},$		21	30	nC
$Q_{gs}$	Gate–Source Charge	$V_{GS} = -4.5\text{ V}$		3.5		nC
$Q_{gd}$	Gate–Drain Charge			4.5		nC

### Drain–Source Diode Characteristics and Maximum Ratings

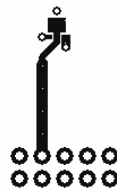
$I_S$	Maximum Continuous Drain–Source Diode Forward Current				1.6	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -0.8\text{ A}$ (Note 2)		-0.6	-1.2	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = -6.8\text{ A},$		26	48	nS
$Q_{rr}$	Diode Reverse Recovery Charge	$dI_F/dt = 100\text{ A}/\mu\text{s}$		12	22	nC

#### Notes:

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



- a)  $65^\circ\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper

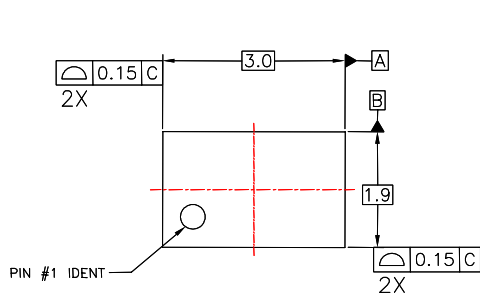


- b)  $208^\circ\text{C/W}$  when mounted on a minimum pad of 2 oz copper

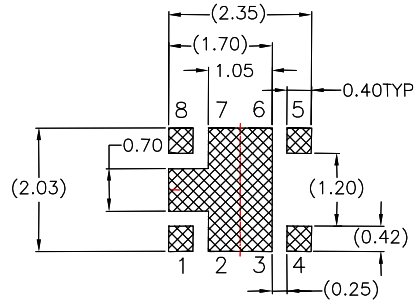
Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width <  $300\ \mu\text{s}$ , Duty Cycle < 2.0%

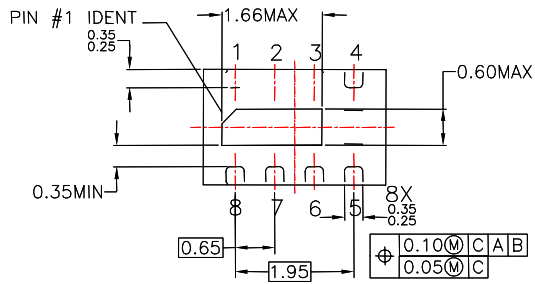
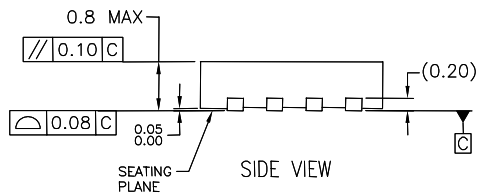
## Dimensional Outline and Pad Layout



TOP VIEW



RECOMMENDED LAND PATTERN



BOTTOM VIEW

### NOTES:

- A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229, DATED 11/2001.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994

## Typical Characteristics

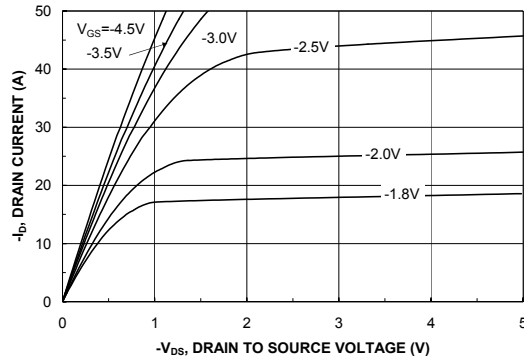


Figure 1. On-Region Characteristics.

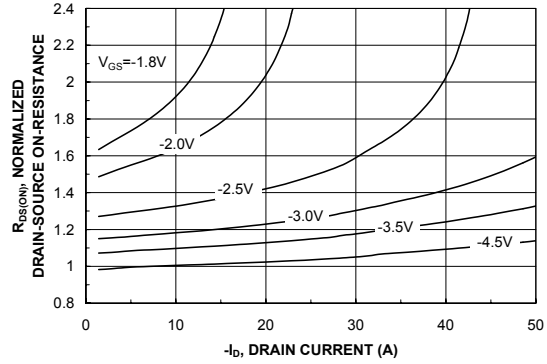


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

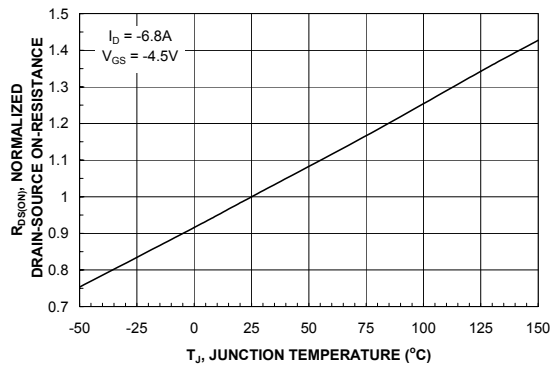


Figure 3. On-Resistance Variation with Temperature.

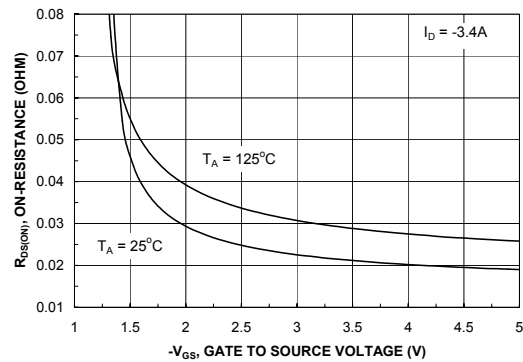


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

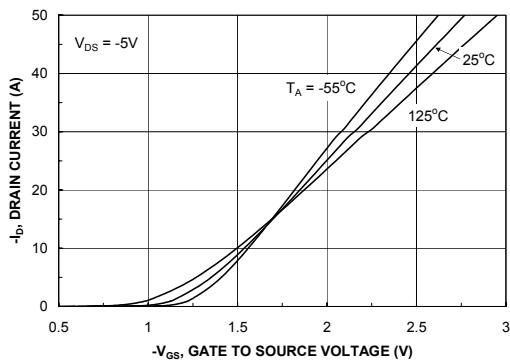


Figure 5. Transfer Characteristics.

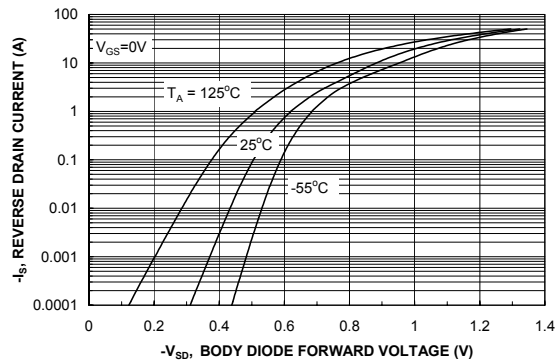
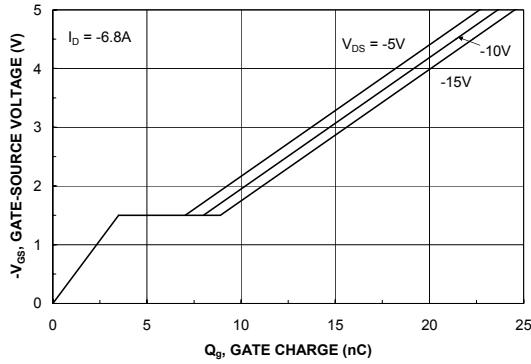
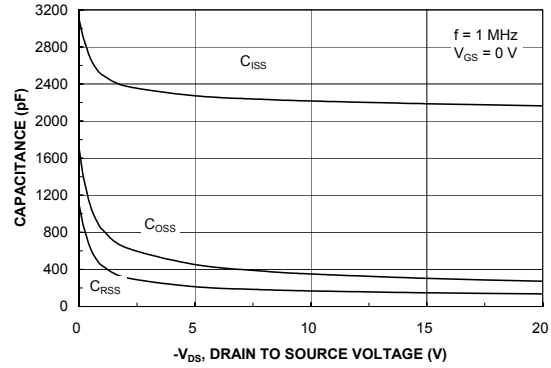


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

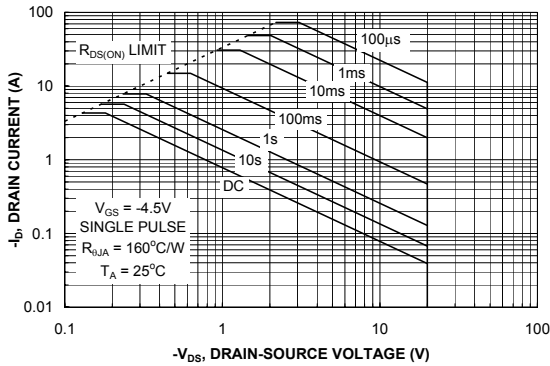
## Typical Characteristics



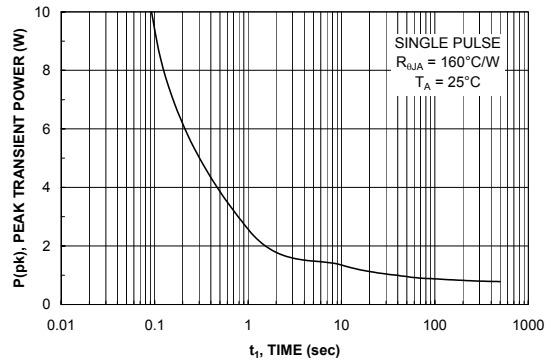
**Figure 7. Gate Charge Characteristics.**



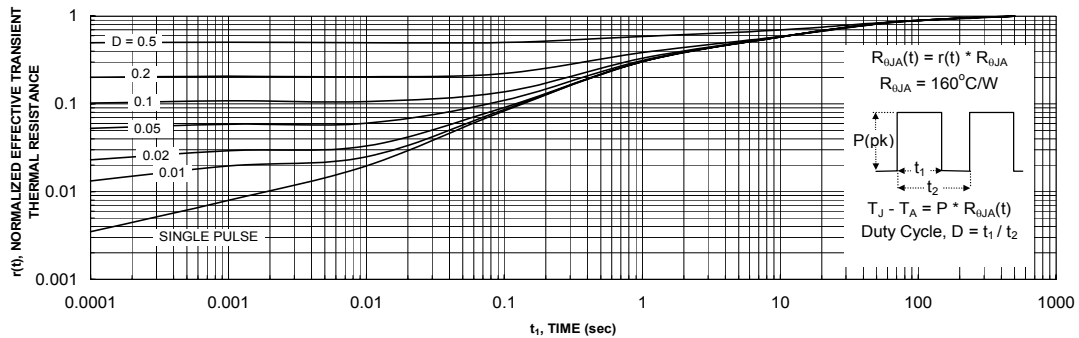
**Figure 8. Capacitance Characteristics.**



**Figure 9. Maximum Safe Operating Area.**



**Figure 10. Single Pulse Maximum Power Dissipation.**



**Figure 9. Transient Thermal Response Curve.**

Thermal characterization performed using the conditions described in Note 1c.  
Transient thermal response will change depending on the circuit board design.

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